

SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

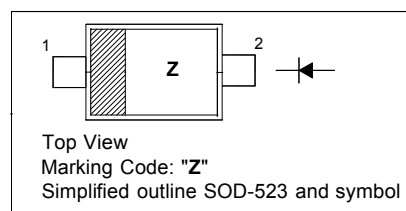
for rectifying small power applications

Features

- Ultra small mold type
- Low forward voltage
- High reliability

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

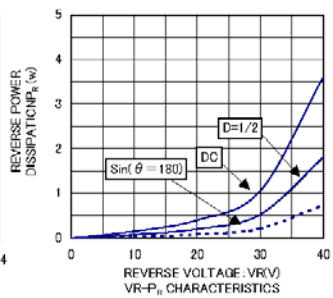
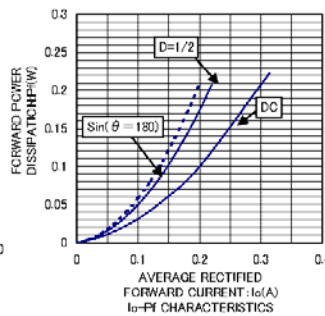
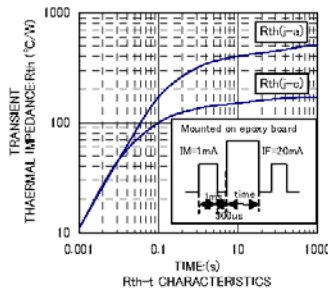
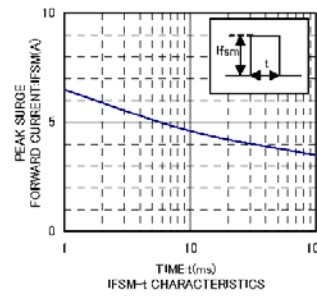
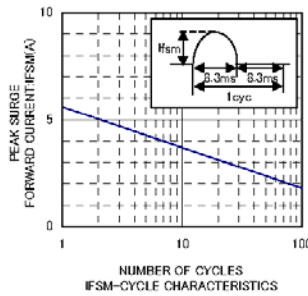
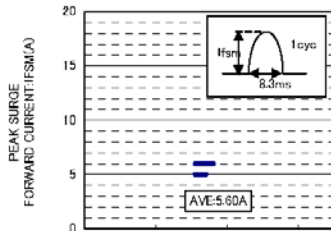
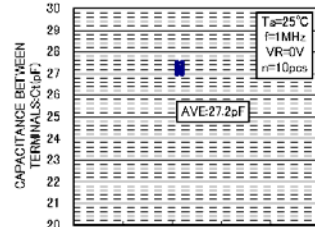
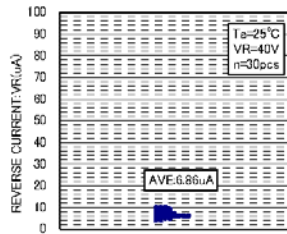
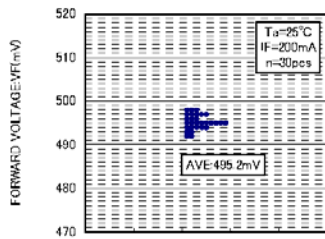
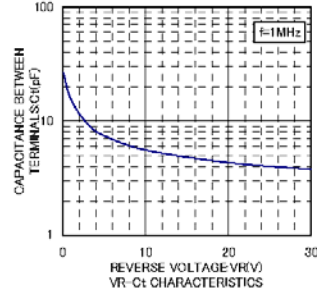
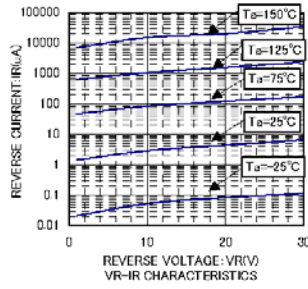
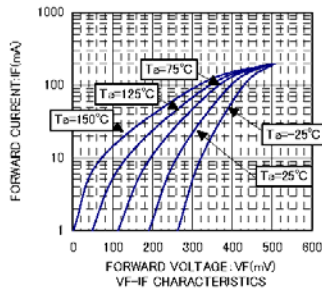


Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RM}	45	V
Reverse Voltage	V_R	40	V
Mean Rectifying Current	I_O	200	mA
Peak Forward Surge Current (60Hz for Cyc.)	I_{FSM}	1	A
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$ at $I_F = 100\text{ mA}$ at $I_F = 200\text{ mA}$	V_F	0.16 0.31 0.41	0.3 0.45 0.54	V
Reverse Current at $V_R = 10\text{ V}$ at $V_R = 40\text{ V}$	I_R	- -	20 90	μA





CHINA BASE
INTERNATIONAL

SOD-523

RB521S-40

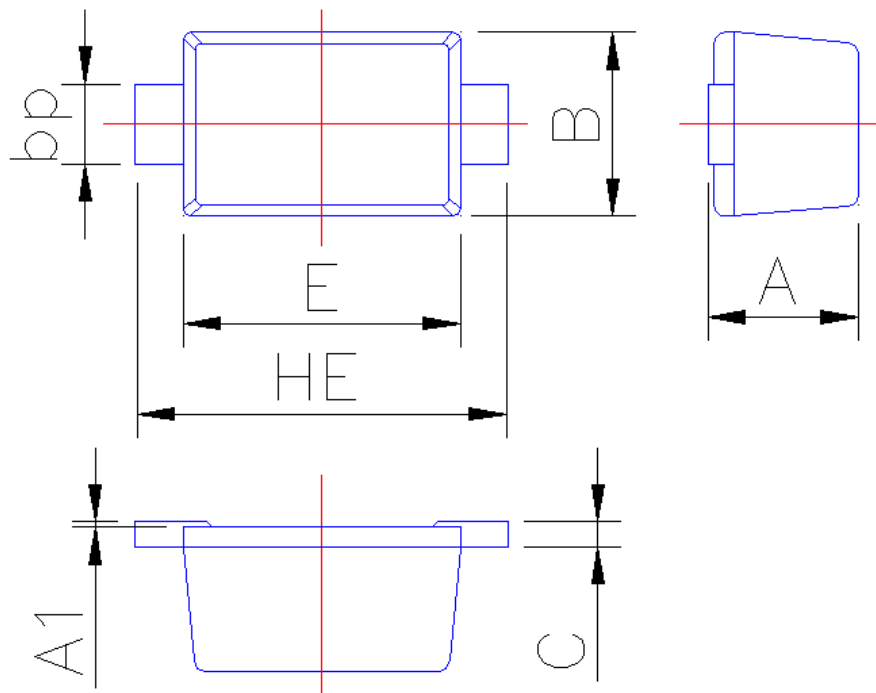


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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



Symbol	Dimension in Millimeters	
	Min	Max
A	0.60	0.70
A1	0	0.05
B	0.75	0.85
bp	0.25	0.40
C	0.09	0.15
E	1.15	1.25
HE	1.50	1.70